METHOD OF FORMING STORAGE NODES IN A DRAM

Appl. No.   : 09/851,580   Confirmation No. 3189

Applicant   : Jiunn-Ren Hwang et al.

Filed   : May 10, 2001

TC/A.U.   : 1795

Examiner   : Ruggles, John S

Docket No. : NAUP0292USA

Customer No. : 27765

Commissioner for Patents

P.O. Box 1450

Alexandria VA 22313-1450

<div align="center">AMENDMENT</div>

Sir:

5   In response to the Office action of July 10, 2008, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 6 of this paper.

10   Amendments to the Drawings begin on page 8 of this paper.

Remarks/Arguments begin on page 9 of this paper.

An Appendix including amended drawing figures is attached following page 11 of this paper.